



# GPDP3276

## AVALANCHE RECTIFIER DIODE

**VOLTAGE UP TO** 1700 - 2000 - 2300 V  
**AVERAGE CURRENT** 2760 A  
**SURGE CURRENT** 29 kA

### BLOCKING CHARACTERISTICS

Characteristic	Conditions	Value
V <sub>RRM</sub>	Repetitive peak reverse voltage	1700 - 2000 - 2300 V
V <sub>RSM</sub>	Non-repetitive peak reverse voltage	V
I <sub>RRM</sub>	Repetitive peak reverse current, max.	V <sub>RRM</sub> , single phase, half wave, T <sub>jmax</sub>
P <sub>RSM</sub>	Peak reverse power, max	T <sub>jmax</sub> , t <sub>p</sub> = 20μs

### FORWARD CHARACTERISTICS

I <sub>F(AV)</sub>	Average forward current	Sine wave, 180° conduction, T <sub>h</sub> = 55°C	2760 A
I <sub>F(RMS)</sub>	R.M.S. forward current	Sine wave, 180° conduction, T <sub>h</sub> = 55°C	4333 A
I <sub>FSM</sub>	Surge forward current	Non rep. half sine wave, 50 Hz, V <sub>R</sub> = 0 V, T <sub>j</sub> = T <sub>jmax</sub>	29 kA
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination		4205 kA <sup>2</sup> s
V <sub>F(TO)</sub>	Threshold voltage	T <sub>j</sub> = T <sub>jmax</sub>	0.84 V
r <sub>F</sub>	Forward slope resistance	T <sub>j</sub> = T <sub>jmax</sub>	0.130 mΩ
V <sub>FM</sub>	Peak forward voltage, max	Forward current I <sub>F</sub> = 4000 A, T <sub>j</sub> = 25°C	1.35 V

### SWITCHING CHARACTERISTICS

Q <sub>rr</sub>	Reverse recovery charge, typ	T <sub>j</sub> = T <sub>jmax</sub> , I <sub>F</sub> = 2000 A, di/dt = -5 A/μs	μC
I <sub>rr</sub>	Reverse recovery current	V <sub>R</sub> = 100 V	A
t <sub>rr</sub>	Reverse recovery time		μs
V <sub>FP</sub>	Forward recovery voltage	T <sub>j</sub> = T <sub>jmax</sub> , di/dt = A/μs	V

### THERMAL AND MECHANICAL CHARACTERISTICS

R <sub>th(j-c)</sub>	Thermal resistance (junction to case)	Double side cooled	0.020 °C/W
R <sub>th(c-h)</sub>	Thermal resistance (case to heatsink)	Double side cooled	0.002 °C/W
T <sub>jmax</sub>	Max operating junction temperature		160 °C
T <sub>stg</sub>	Storage temperature		-40 / 160 °C
F	Clamping force ± 10%		22 kN
	Mass		500 g